

MMBF2202PT1

These miniature surface mount MOSFETs low $R_{DS(on)}$ assure minimal power loss and conserve energy, making these devices ideal for use in small power management circuitry. Typical applications are dc-dc converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low R_{DS(on)} Provides Higher Efficiency and Extends Battery Life
- Miniature SC-70/SOT-323 Surface Mount Package Saves Board Space
- Pb-Free Package is Available

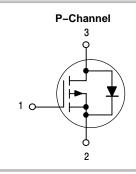
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	20	Vdc
Gate-to-Source Voltage - Continuous	V_{GS}	± 20	Vdc
	I _D I _D	300 240 750	mAdc
Total Power Dissipation @ T _A = 25°C (Note 1) Derate above 25°C	P _D	150 1.2	mW mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T_L	260	°C

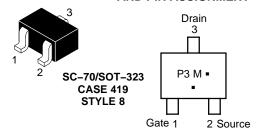
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

 Mounted on G10/FR4 glass epoxy board using minimum recommended footprint.

300 mAMPS, 20 VOLTS $R_{DS(on)} = 2.2 \Omega$



MARKING DIAGRAM AND PIN ASSIGNMENT



P3 = Specific Device Code

M = Date Code*

■ = Pb-Free Package (Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBF2202PT1	SC-70/ SOT-323	3000 Tape & Reel
MMBF2202PT1G	SC-70/ SOT-323 (Pb-Free)	3000 Tape & Reel



Product specification

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

MMBF2202PT1

Char	acteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 10 μA)	Э	V _{(BR)DSS}	20	-	_	Vdc
Zero Gate Voltage Drain Current $(V_{DS} = 16 \text{ Vdc}, V_{GS} = 0 \text{ Vdc})$ $(V_{DS} = 16 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, T_{JS})$	= 125°C)	I _{DSS}		_ _	1.0 10	μAdc
Gate-Body Leakage Current (V _{GS} =	\pm 20 Vdc, V _{DS} = 0)	I _{GSS}	_	_	±100	nAdc
ON CHARACTERISTICS (Note 2)		·				
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 250 \mu Adc)$		V _{GS(th)}	1.0	1.7	2.4	Vdc
Static Drain-to-Source On-Resistal ($V_{GS} = 10 \text{ Vdc}$, $I_D = 200 \text{ mAdc}$) ($V_{GS} = 4.5 \text{ Vdc}$, $I_D = 50 \text{ mAdc}$)	nce	r _{DS(on)}		1.5 2.0	2.2 3.5	Ω
Forward Transconductance (V _{DS} = 1	10 Vdc, I _D = 200 mAdc)	9FS	_	600	_	mMhos
DYNAMIC CHARACTERISTICS		•				
Input Capacitance	(V _{DS} = 5.0 V)	C _{iss}	_	50	_	pF
Output Capacitance	(V _{DS} = 5.0 V)	C _{oss}	_	45	_	
Transfer Capacitance	(V _{DG} = 5.0 V)	C _{rss}	_	20	_	
SWITCHING CHARACTERISTICS (Note 3)						
Turn-On Delay Time		t _{d(on)}	_	2.5	_	ns
Rise Time	$(V_{DD} = -15 \text{ Vdc}, \\ R_L = 75 \ \Omega, \ I_D = 200 \text{ mAdc}, \\ V_{GEN} = -10 \ V, \ R_G = 6.0 \ \Omega)$	t _r	_	1.0	_	
Turn-Off Delay Time		t _{d(off)}	_	16	_	
Fall Time		t _f	_	8.0	_	
Gate Charge (See Figure 5)	$(V_{DS} = 16 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 200 \text{ mA})$	Q _T	-	2700	_	рС
SOURCE-DRAIN DIODE CHARAC	TERISTICS				•	
Continuous Current		Is	_	-	0.3	А
Pulsed Current		I _{SM}	_	_	0.75	
Forward Voltage (Note 3)		V _{SD}	_	1.5	_	V

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.